



This technology is currently not available for licensing

Tech ID: 25742

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Ultraviolet Laser Diode on Nano-Porous AlGaIn template
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ Thermally Stable, Laser-Driven White Lighting Device
- ▶ Methods for Fabricating III-Nitride Tunnel Junction Devices
- ▶ Contact Architectures for Tunnel Junction Devices
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ▶ High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact

